

Description

The PPM8PN30V25 uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge. This device is suitable for use as a load switch or in PWM applications.

MOSFET Product Summary

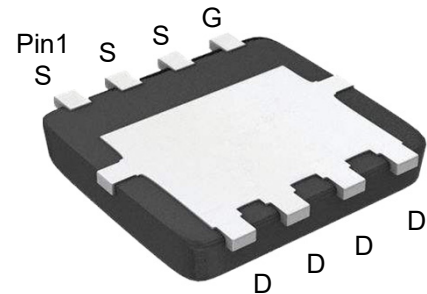
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
-30	11@ $V_{GS} = -10V$	-37
	15@ $V_{GS} = -4.5V$	

Feature

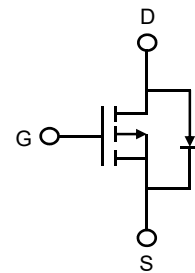
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Applications

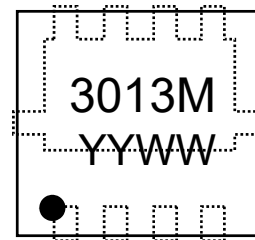
- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers



Bottom View



Circuit Diagram



Pin1

Marking (Top View)

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-37	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	-140	A
Total Power Dissipation	P_D	35.6	W
Avalanche Current ⁽²⁾	I_{AS}	-36.5	A
Avalanche Energy ⁽²⁾	E_{AS}	66.74	mJ
Thermal Resistance , Junction-case ⁽³⁾	$R_{\theta JC}$	7.87	°C/W
Thermal Resistance Junction-to-Ambient ⁽³⁾	$R_{\theta JA}$	44.8	°C/W
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$	-	-	-1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics⁴⁾						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.6	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -7A$	-	11	15	m Ω
		$V_{GS} = -4.5V, I_D = -6A$	-	15	20	
Forward Transconductance	g_{FS}	$V_{DS} = -10V, I_D = -10A$	20	-	-	S
Dynamic Characteristics⁵⁾						
Input Capacitance	C_{ISS}	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.0MHz$	-	1207	-	pF
Output Capacitance	C_{OSS}		-	170	-	
Reverse Transfer Capacitance	C_{RSS}		-	146	-	
Switching Characteristics⁵⁾						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = -15V, V_{GS} = -10V,$ $R_G = 1\Omega, I_D = -10A$	-	10	-	ns
Turn-on Rise Time	t_r		-	5.5	-	
Turn-Off Delay Time	$t_{d(off)}$		-	26	-	
Turn-Off Fall Time	t_f		-	9.0	-	
Total Gate Charge	Q_g	$V_{DS} = -15V, V_{GS} = -10V,$ $I_D = -10A$	-	25.8	-	nC
Gate-Source Charge	Q_{gs}		-	3.9	-	
Gate-Drain Charge	Q_{gd}		-	5.2	-	
Drain-Source Diode Characteristics						
Diode Forward Voltage ⁴⁾	V_{SD}	$V_{GS} = 0V, I_S = -2A$	-0.4	-	-1.0	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
3. This single-pulse measurement was taken under the following condition [$L=100\mu H, V_{GS}=-10V, V_{DS}=-30V$] while it's value is limited by $T_{J_Max}=150^\circ C$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycles $\leq 2\%$.
5. Guaranteed by design, not subject to production.

Typical Characteristics

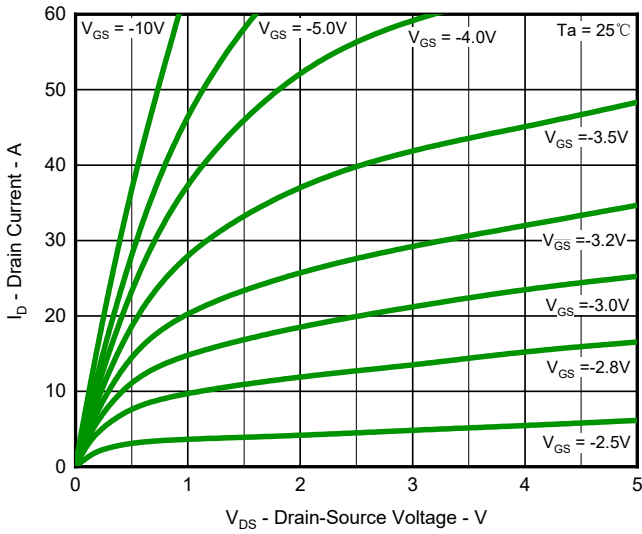


Fig.1 Output Characteristics

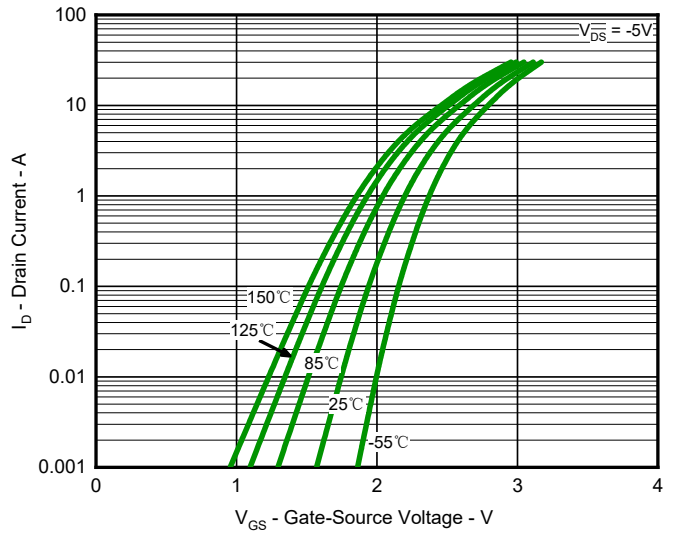


Fig.2 Typical Transfer Characteristic

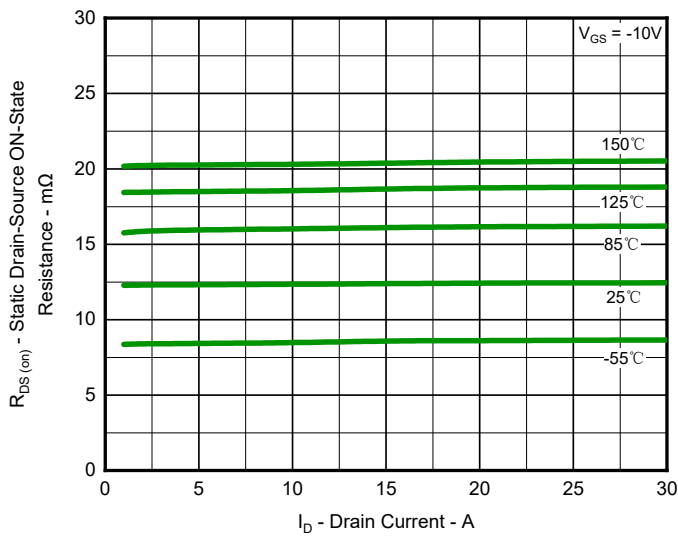


Fig.3 Typical On-Resistance vs Drain Current and Temperature

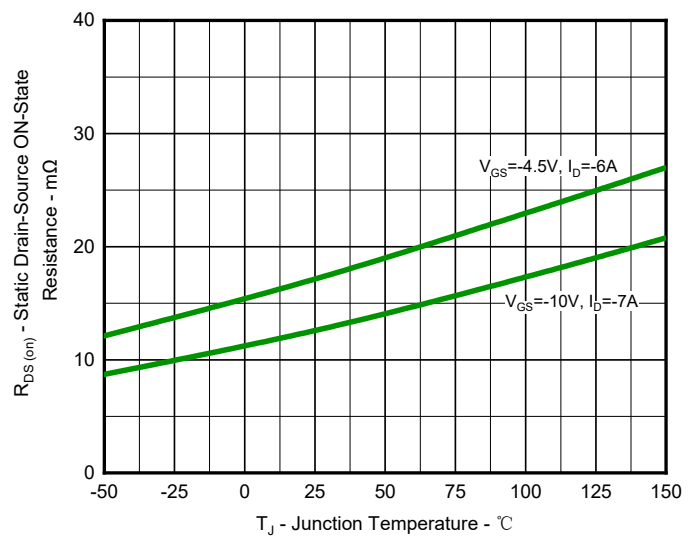


Fig.4 On-Resistance Variation with Temperature

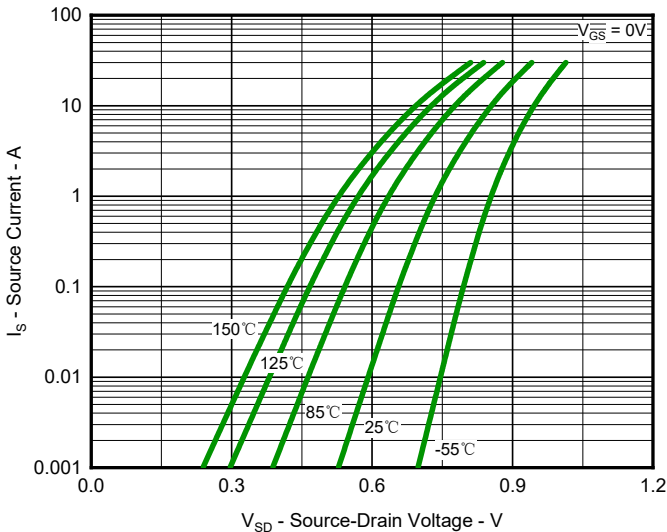


Fig.5 Diode Forward Voltage vs. Current

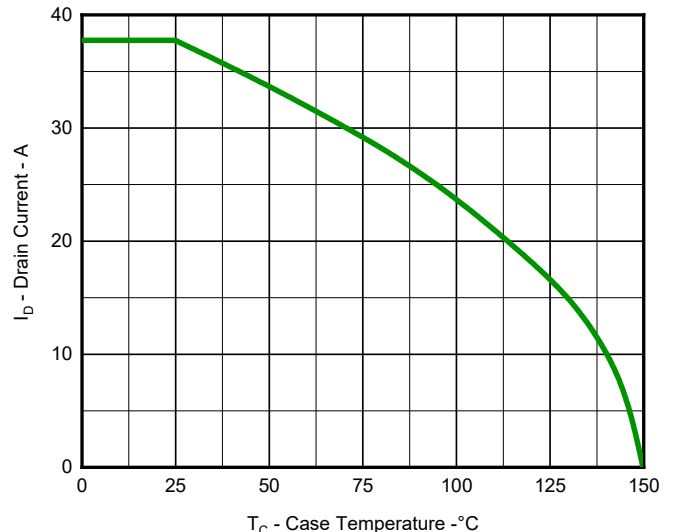


Fig.6 Maximum Drain Current vs. Case Temperature

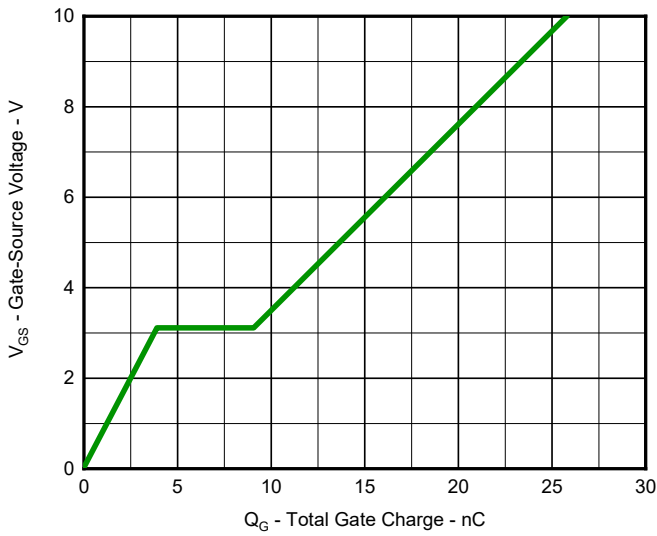


Fig.7 Gate Charge Characteristics

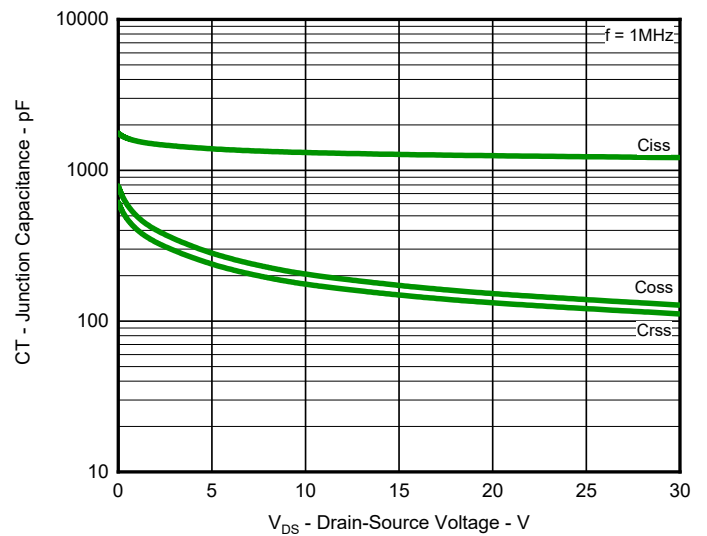


Fig.8 Typical Junction Capacitance

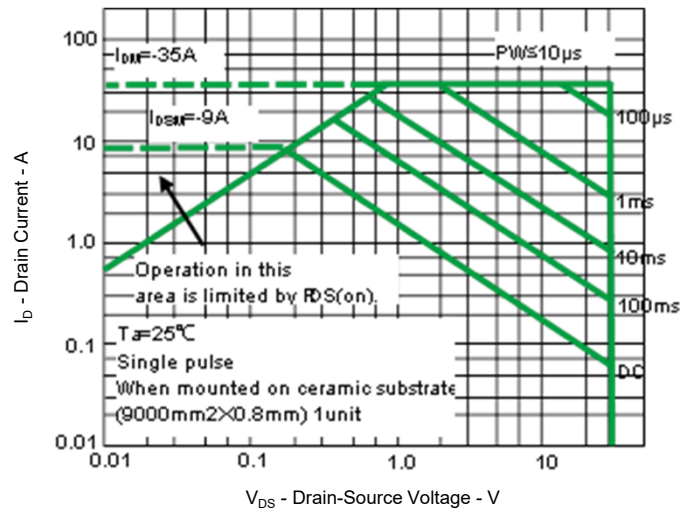


Fig.9 Safe Operation Area

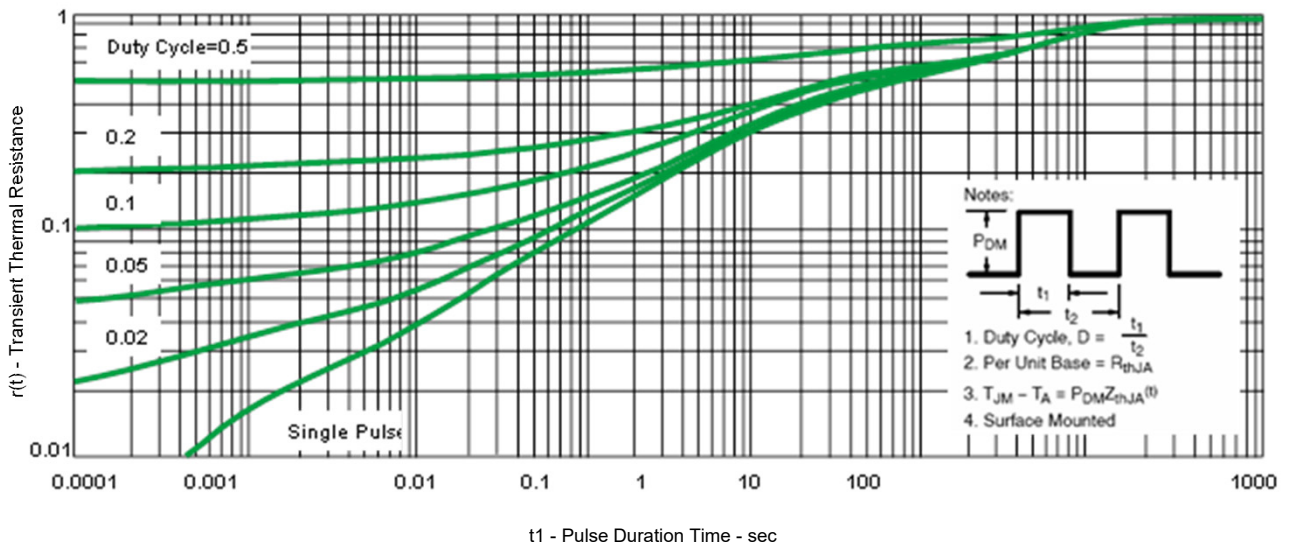
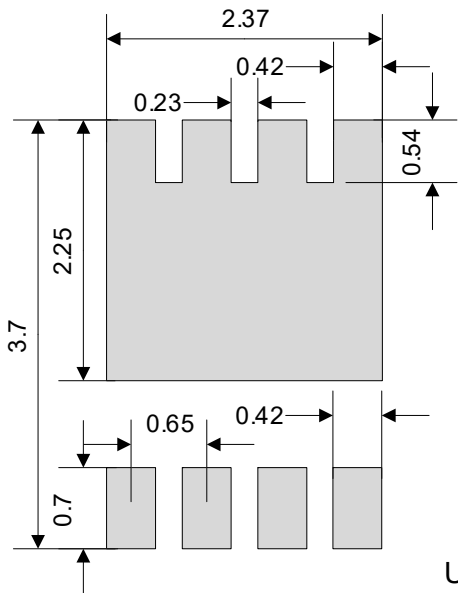
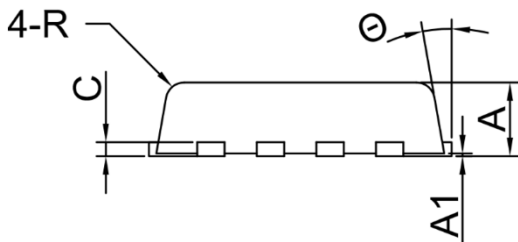
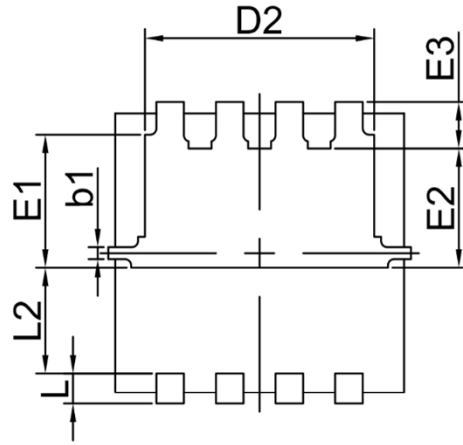
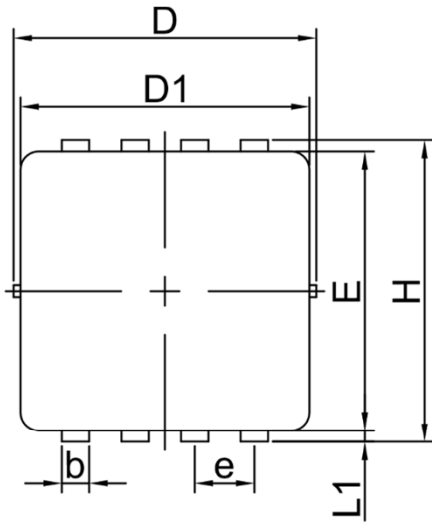


Fig.10 Transient Thermal Resistance

Product Dimension (DFN3333-8L)



Unit:mm

Suggested PCB Layout

Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	0.70	0.80	0.028	0.031
A1	0.00	0.05	0.000	0.002
b	0.24	0.35	0.009	0.014
b1	0.08	0.18	0.003	0.007
c	0.152 Ref.		0.006 Ref.	
D	3.25	3.40	0.128	0.134
D1	3.05	3.25	0.120	0.128
D2	2.40	2.60	0.094	0.102
E	3.00	3.20	0.118	0.126
E1	1.35	1.55	0.053	0.061
E2	1.20	1.40	0.047	0.055
E3	0.40	0.60	0.016	0.024
e	0.65 BSC		0.026 BSC	
H	3.20	3.40	0.126	0.134
L	0.30	0.50	0.012	0.020
L1	0.10	0.20	0.004	0.008
L2	1.13 Ref.		0.044 Ref.	
R	0.20 Ref.		0.008 Ref.	
θ	6°	14°	6°	14°

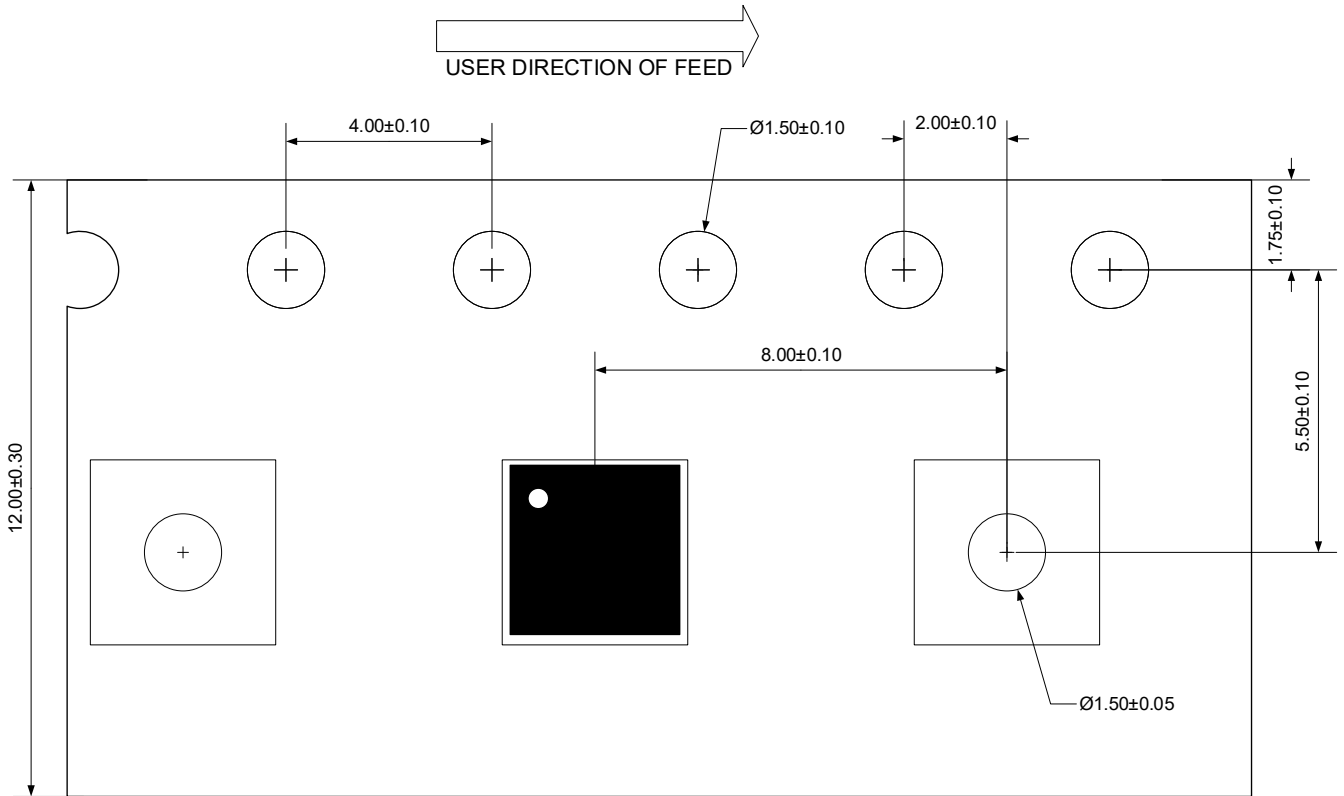
P-Channel MOSFET

PPM8PN30V25

Ordering Information


Device	Package	Reel	Shipping
PPM8PN30V25	PDFN3333-8L(Pb-Free)	13"	5000 / Tape & Reel

Load With Information



Unit:mm


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